

Ion implantation range data for silicon and germanium device technologies

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Ion implantation is a low-temperature process by which one element is accelerated into a solid target, thereby changing the physical, chemical, or electrical properties of the target. When implanted in a semiconductor, each dopant atom can create a charge carrier in the semiconductor after. Communication device for a logic circuit 1998-02-13 2006-05-30 Micron Technology, Inc.

Polymers as masks for Ion implantation

The ion implantation technique is used to dope boron selectively into the N- type collector layer 76. However, the gallium-arsenide high-electron mobility materials come with a serious technical problem: It is very difficult to make a gate insulation layer of high quality, which has been easily obtained in the metal oxide semiconductor field effect transistors MOSFETs using one of the most popular semiconductor materials, i.

ION IMPLANTATION OF SILICON AND GERMANIUM AT ROOM TEMPERATURE. ANALYSIS BY MEANS OF 1.0

Semiconductor device and method for fabricating the same 2002-01-09 2006-12-05 Matsushita Electric Industrial Co.

Table III from Modeling of boron and phosphorus implantation into (100) Germanium

Semiconductor device 1998-02-05 2010-03-02 Semiconductor Energy Laboratory Co.

Ge ion implantation in Si for the fabrication of Si/GexSi1

Ions gradually lose their energy as they travel through the solid, both from occasional collisions with target atoms which cause abrupt energy transfers and from a mild drag from overlap of electron orbitals, which is a continuous process.

ION IMPLANTATION OF SILICON AND GERMANIUM AT ROOM TEMPERATURE. ANALYSIS BY MEANS OF 1.0

The particles may be formed as a result of precipitation of the ion implanted species, they may be formed as a result of the production of an mixed oxide species that contains both the ion-implanted element and the oxide substrate, and they may be formed as a result of a reduction of the substrate, first reported by Hunt and Hampikian. The holes moving inside this second channel region are prevented by the potential barrier from coming into collision with the gate insulation layer 18. These losses are inevitable if the conventional ion implantation and diffusion methods are employed.

Germanium ion implantation for trimming the coupling efficiency of silicon racetrack resonators

Interstitials result when such atoms or the original ion itself come to rest in the solid, but find no vacant space in the lattice to reside.

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